

# Surface Mount - 800V > BTA12-600CW3G, BTA12-800CW3G,

#### **Maximum Ratings** ( $T_{J} = 25^{\circ}C$ unless otherwise noted)

Rating	Symbol	Value	Unit
Peak Repetitive Off-State Voltage (Note 1) (Gate Open, Sine Wave 50 to 60 Hz, T <sub>J</sub> = -40° to 125°C) BTA12–600CW3G BTA12–800CW3G	V <sub>drm</sub> , V <sub>rrm</sub>	600 800	V
On-State RMS Current (Full Cycle Sine Wave, 60 Hz, $T_c = 80^{\circ}$ C)	I <sub>T (RMS)</sub>	12	А
Peak Non-Repetitive Surge Current (One Full Cycle Sine Wave, 60 Hz, T <sub>c</sub> = 25°C)	I <sub>TSM</sub>	105	А
Circuit Fusing Consideration (t = $8.3 \text{ ms}$ )	l²t	46	A <sup>2</sup> sec
Non–Repetitive Surge Peak Off–State Voltage ( $T_J = 25^{\circ}C$ , t = 10ms)	V <sub>DSM</sub> /V <sub>RSM</sub>	V <sub>DSM</sub> /V <sub>RSM</sub> +100	V
Peak Gate Current ( $T_J = 125^{\circ}C$ , t = 20ms)	I <sub>GM</sub>	4.0	А
Peak Gate Power (Pulse Width $\leq$ 1.0 µs, T <sub>c</sub> = 80°C)	P <sub>G(AV)</sub>	20	W
Average Gate Power ( $T_J = 125^{\circ}C$ )	P <sub>G(AV)</sub>	1.0	W
Operating Junction Temperature Range	TJ	-40 to +125	°C
Storage Temperature Range	T <sub>stg</sub>	-40 to +125	°C
RMS Isolation Voltage (t = 300 ms, R.H. $\leq$ 30%, T <sub>A</sub> = 25°C)	V <sub>iso</sub>	2500	V

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. V<sub>DRM</sub> and V<sub>RRM</sub> for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; however, positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

Thermal Characteristics					
Rating		Symbol	Value	Unit	
Thermal Resistance,	Junction-to-Case (AC) Junction-to-Ambient	R <sub>sjc</sub> R <sub>sja</sub>	2.5 60	°C/W	
Maximum Lead Temperature for Soldering Purposes, 1/8" from case for 10 seconds		TL	260	°C	



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#### Electrical Characteristics • OFF (T<sub>1</sub> = 25°C unless otherwise noted ; Electricals apply in both directions)

Characteristic		Symbol	Min	Тур	Max	Unit
Peak Repetitive Blocking Current	$T_{J} = 25^{\circ}C$	I <sub>DRM</sub> ,	-	-	0.005	
$(V_{D} = V_{DRM} = V_{RRM}; \text{ Gate Open})$	T <sub>J</sub> = 125°C	I RRM	-	-	2.0	mA

# **Electrical Characteristics** - **ON** ( $T_{J} = 25^{\circ}$ C unless otherwise noted; Electricals apply in both directions)

Characteristic		Symbol	Min	Тур	Max	Unit
Forward On-State Voltage (Note 2) ( $I_{TM} = \pm 17$ A Peak)		V <sub>TM</sub>	-	_	1.55	V
Gate Trigger Current (Continuous dc) ( $V_p = 12 \text{ V}, \text{ R}_L = 30 \Omega$ )	MT2(+), G(+)		2.0	_	35	
	MT2(+), G(-)	I <sub>GT</sub>	2.0	-	35	mA
	MT2(-), G(-)		2.0	-	35	
Holding Current ( $V_p = 12 V$ , Gate Open, Initiating Current = ±100 mA)		I <sub>H</sub>	_	_	45	mA
	MT2(+), G(+)		-	_	50	
Latching Current (V <sub>D</sub> = 24 V, I <sub>G</sub> = 42 mA)	MT2(+), G(-)	I.	_	_	80	mA
	MT2(-), G(-)		-	_	50	
	MT2(+), G(+)		0.5	-	1.7	
Gate Trigger Voltage (V $_{\rm D}$ = 12 V, R $_{\rm L}$ = 30 $\Omega)$	MT2(+), G(-)	V <sub>GT</sub>	0.5	_	1.1	V
	MT2(-), G(-)		0.5	_	1.1	
	MT2(+), G(+)		0.2	-	-	
Gate Non–Trigger Voltage ( $T_J = 125^{\circ}C$ )	MT2(+), G(-)	V <sub>gD</sub>	0.2	_	-	V
	MT2(–), G(–)		0.2	_	_	

2. Indicates Pulse Test: Pulse Width  $\leq$  2.0 ms, Duty Cycle  $\leq$  2%.



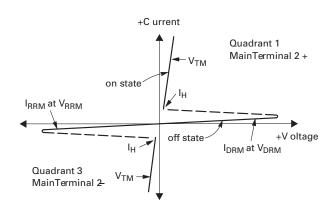
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#### **Dynamic Characteristics**

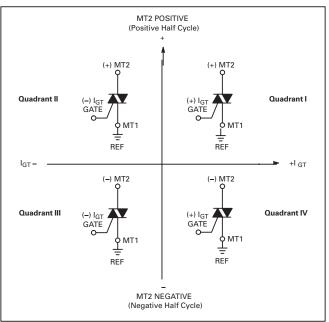
Characteristic	Symbol	Min	Тур	Max	Unit
Rate of Change of Commutating Current, See Figure 10. (Gate Open, T <sub>J</sub> = 125°C, No Snubber)	(dl/dt)c	2.5	-	-	A/ms
Critical Rate of Rise of On–State Current ( $T_J = 125^{\circ}C$ , f = 120 Hz, $I_G = 2 \times I_{GT}$ , tr $\leq$ 100 ns)	dl/dt	-	-	50	A/µs
Critical Rate of Rise of Off-State Voltage ( $V_D = 0.66 \times V_{DRM}$ , Exponential Waveform, Gate Open, $T_J = 125^{\circ}C$ )	dV/dt	2000	-	_	V/µs

#### Voltage Current Characteristic of SCR

Symbol	Parameter
V <sub>drm</sub>	Peak Repetitive Forward Off State Voltage
I	Peak Forward Blocking Current
V <sub>RRM</sub>	Peak Repetitive Reverse Off State Voltage
I <sub>RRM</sub>	Peak Reverse Blocking Current
V <sub>TM</sub>	Maximum On State Voltage
I <sub>H</sub>	Holding Current



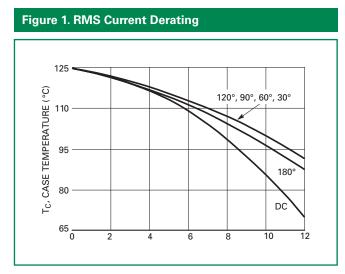
#### **Quadrant Definitions for a Triac**



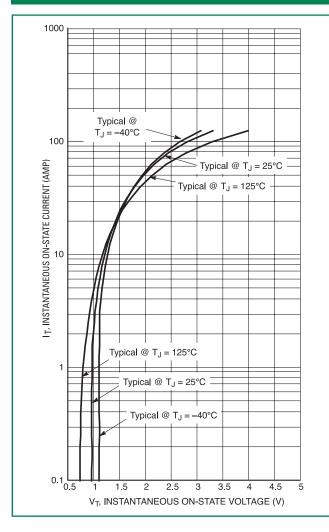
All polarities are referenced to MT1. With in-phase signals (using standard AC lines) quadrants I and III are used.



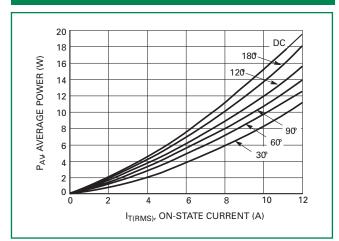
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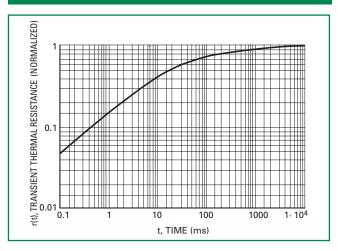
#### Figure 3. On–State Characteristics



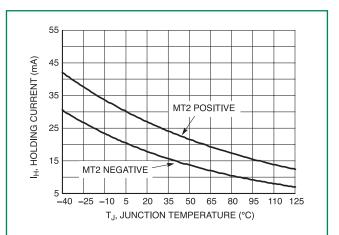
#### Figure 2. On-State Power Dissipation



#### Figure 4. Thermal Response

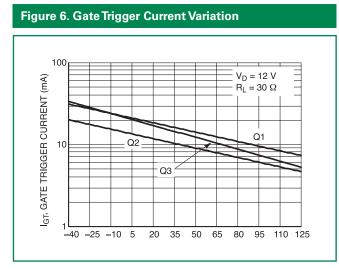


#### Figure 5. Hold Current Variation

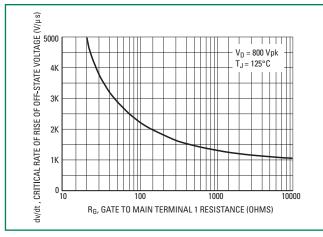




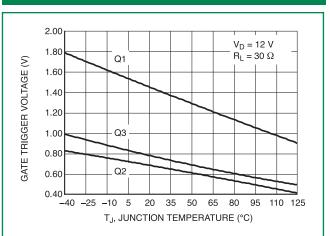
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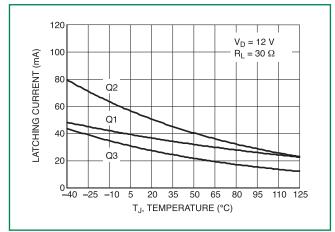
# Figure 8. Critical Rate of Rise of Off-State Voltage (Exponential Waveform)



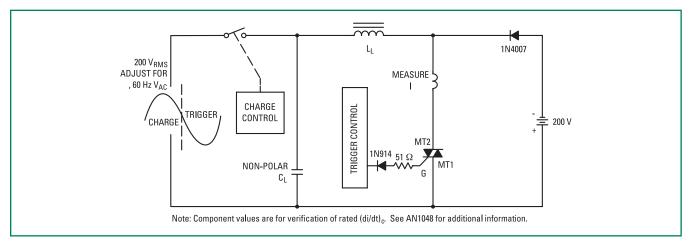
#### Figure 7. Gate Trigger Voltage Variation



#### Figure 10. Latching Current Variation



#### Figure 9. Simplified Test Circuit to Measure the Critical Rate of Rise of Commutating Current (di/dt)



Note: Component values are for verification of rated (di/dt)c. See AN1048 for additional information



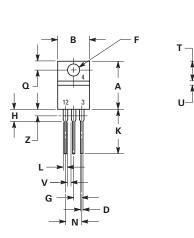
-T- SEATING PLANE

S

R

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#### Dimensions



<b>C</b> .	Dim Inches Min Max		Millimeters		
Dim			Min	Max	
А	0.570	0.620	14.48	15.75	
В	0.380	0.405	9.66	10.28	
С	0.160	0.190	4.07	4.82	
D	0.025	0.035	0.64	0.88	
F	0.142	0.147	3.61	3.73	
G	0.095	0.105	2.42	2.66	
Н	0.110	0.155	2.80	3.93	
J	0.014	0.022	0.36	0.55	
Κ	0.500	0.562	12.70	14.27	
L	0.045	0.060	1.15	1.52	
Ν	0.190	0.210	4.83	5.33	
Q	0.100	0.120	2.54	3.04	
R	0.080	0.110	2.04	2.79	
S	0.045	0.055	1.15	1.39	
Т	0.235	0.255	5.97	6.47	
U	0.000	0.050	0.00	1.27	
V	0.045		1.15		
Z		0.080		2.04	

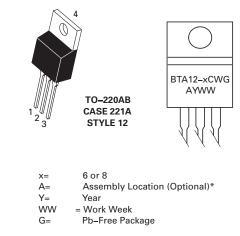
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

2. CONTROLLING DIMENSION: INCH.

3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

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#### Part Marking System



\* The Assembly Location code (A) is optional. In cases where the Assembly Location is stamped on the package the assembly code may be blank.

Pin Assignment	
1	Main Terminal 1
2	Main Terminal 2
3	Gate
4	No Connection

#### **Ordering Information**

Device	Package	Shipping
BTA12-600BW3G	TO-220AB (Pb-Free)	50 Units / Rail
BTA12-800BW3G	TO-220AB (Pb-Free)	50 Units / Rail